



RF360
Europe GmbH

Data sheet

SAW duplexer
Small cell & femtocell
LTE band 66

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Ordering code: B39222B8206P810

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1 Application

- Low-loss SAW duplexer for 3G/LTE small cell & femtocell systems
- Usable pass band 70/90 MHz
- High power durability
- High isolation
- RX = Uplink = 1710 MHz – 1780 MHz
- TX = Downlink = 2110 MHz – 2200 MHz

2 Features

- Industrial grade qualified family
- Package size $2.5_{\pm 0.1}$ mm \times $2.0_{\pm 0.1}$ mm
- Package height 0.5 mm (max.)
- Approximate weight 0.01 g
- RoHS compatible
- Package for Surface Mount Technology (SMT)
- Ni/Au-plated terminals
- Electrostatic Sensitive Device (ESD)
- Moisture Sensitivity Level 2a (MSL2a)

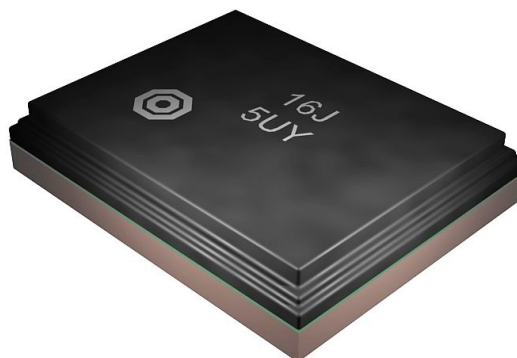
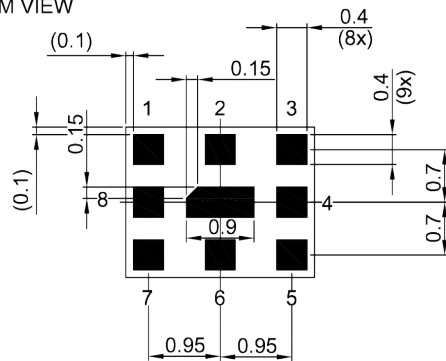


Figure 1: Picture of component with example of product marking.

3 Package

BOTTOM VIEW

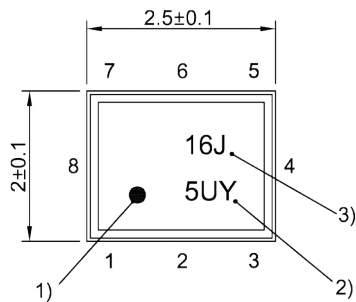


Pad and pitch tolerance ± 0.05

SIDE VIEW

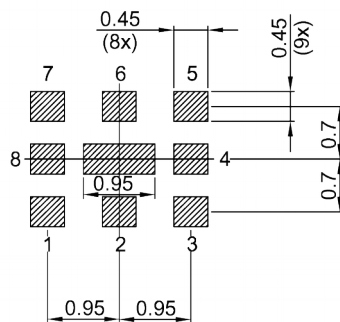


TOP VIEW



- 1) Marking for pad number 1
- 2) Example of encoded lot number
- 3) Example of encoded filter type number

Land pattern
THRU VIEW



Landing pad tolerance -0.02

4 Pin configuration

- 1 TX
- 3 RX
- 6 ANT
- 2, 4, 5, 7, 8, 9 Ground

Figure 2: Drawing of package with package height A = 0.5 mm (max.). See Sec. Package information (p. 28).

5 Matching circuit

■ $L_{p1} = 5.5 \text{ nH}$

■ $L_{p3} = 9.7 \text{ nH}$

■ $L_{p6} = 2.7 \text{ nH}$

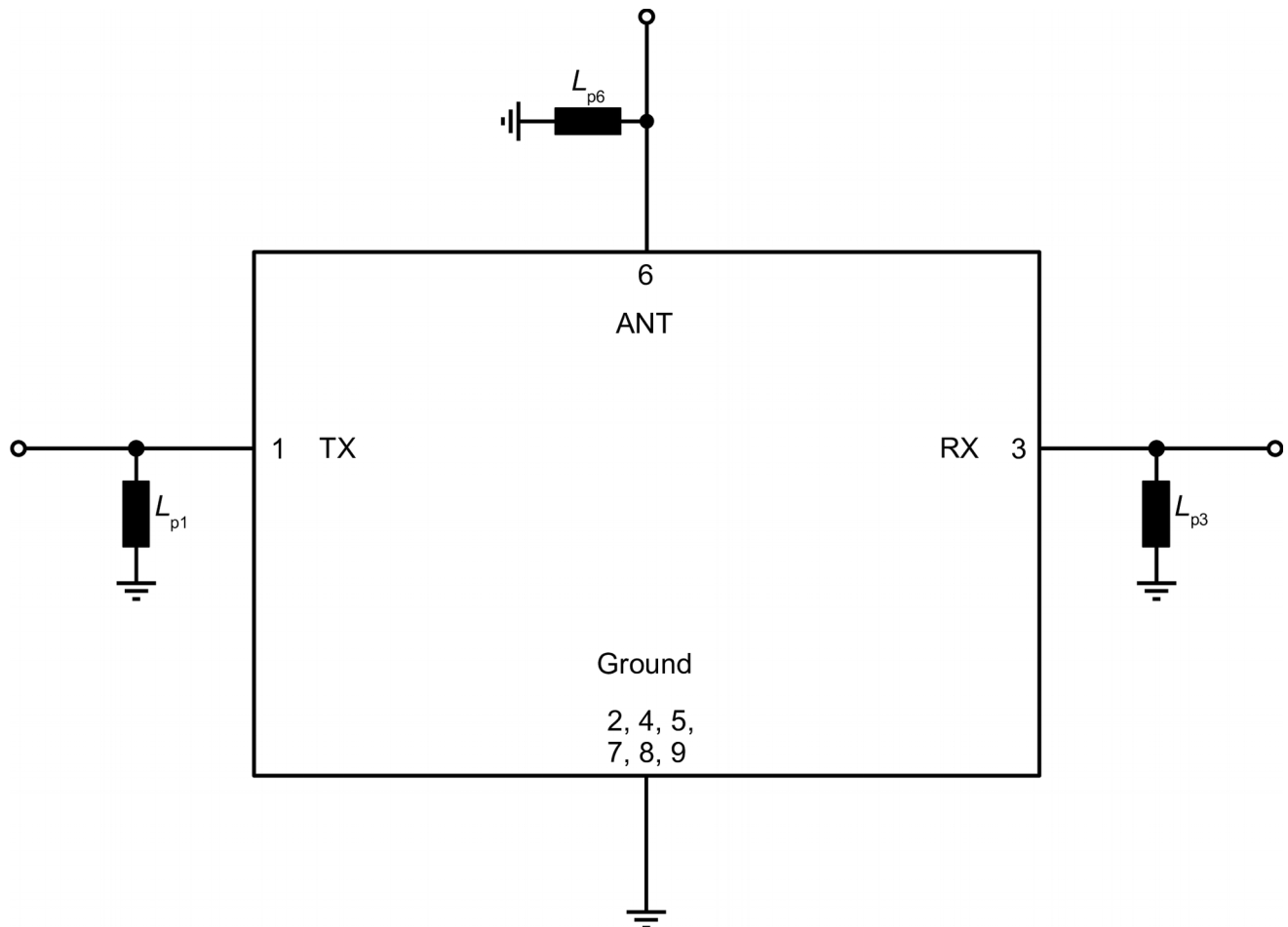


Figure 3: Schematic of matching circuit.

6 Characteristics

6.1 TX – ANT

Temperature range for specification	T_{SPEC}	= -10 °C ... +85 °C
TX terminating impedance	Z_{TX}	= 50 Ω // 5.5 nH ¹⁾
ANT terminating impedance	Z_{ANT}	= 50 Ω // 2.7 nH ¹⁾
RX terminating impedance	Z_{RX}	= 50 Ω // 9.7 nH ¹⁾

Characteristics TX – ANT				min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Center frequency			f_{C}	—	2155	—	MHz
Insertion attenuation			$\alpha_{\text{INT}}^{2)}$				
	2110... 2115	MHz		—	2.4	2.8	dB
	2115... 2195	MHz		—	2.2	2.6	dB
	2195... 2200	MHz		—	2.1	2.8	dB
Maximum insertion attenuation			α_{max}				
	2110... 2200	MHz		—	2.5	3.0	dB
Amplitude ripple (p-p)			$\Delta\alpha$				
	2110... 2200	MHz		—	1.0	1.8	dB
Maximum group delay			t_{max}				
	2112.5... 2197.5	MHz		—	16	30	ns
Group delay ripple			$\Delta\tau_{\text{var}}$				
	2112.5... 2197.5	MHz		—	7	20	ns
Maximum VSWR			VSWR_{max}				
@ TX port	2110... 2200	MHz		—	1.6	2.0	
@ ANT port	2110... 2200	MHz		—	1.5	2.0	
Maximum error vector magnitude			$\text{EVM}_{\text{max}}^{3)}$				
	2112.5... 2197.5	MHz		—	0.7	2.4	%
Minimum attenuation			α_{min}				
	50... 824	MHz		40	61	—	dB
	824... 849	MHz		40	60	—	dB
	849... 1710	MHz		40	50	—	dB
	1710... 1780	MHz		48	51	—	dB
	1780... 1850	MHz		30	47	—	dB
	1850... 1910	MHz		38	41	—	dB
	1910... 1990	MHz		35	37	—	dB
	1990... 2065	MHz		30	37	—	dB
	2240... 2400	MHz		20	46	—	dB
	2400... 2483	MHz		40	43	—	dB
	2483... 4600	MHz		28	32	—	dB
	4600... 5150	MHz		20	29	—	dB
	5150... 5850	MHz		20	28	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

²⁾ Integrated attenuation α_{INT} : Averaged power $|S_{ij}|^2$ over the center 4.5 MHz of LTE 5 MHz (25 RB) channels.

³⁾ Error Vector Magnitude (EVM) based on definition in 3GPP TS 25.141.

Temperature range for specification	T_{SPEC}	= -40 °C ... +95 °C
TX terminating impedance	Z_{TX}	= 50 Ω // 5.5 nH ¹⁾
ANT terminating impedance	Z_{ANT}	= 50 Ω // 2.7 nH ¹⁾
RX terminating impedance	Z_{RX}	= 50 Ω // 9.7 nH ¹⁾

Characteristics TX – ANT				min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Insertion attenuation				α_{INT} ²⁾			
	2110... 2115	MHz		—	2.4	3.0	dB
	2115... 2195	MHz		—	2.2	2.8	dB
	2195... 2200	MHz		—	2.1	3.0	dB
Maximum insertion attenuation				α_{max}			
	2110... 2200	MHz		—	2.5	3.3	dB
Amplitude ripple (p-p)				$\Delta\alpha$			
	2110... 2200	MHz		—	1.0	2.0	dB
Maximum group delay				t_{max}			
	2112.5... 2197.5	MHz		—	16	30	ns
Group delay ripple				$\Delta\tau_{\text{var}}$			
	2112.5... 2197.5	MHz		—	7	20	ns
Maximum VSWR				VSWR_{max}			
@ TX port	2110... 2200	MHz		—	1.6	2.0	
@ ANT port	2110... 2200	MHz		—	1.5	2.0	
Maximum error vector magnitude				EVM_{max} ³⁾			
	2112.5... 2197.5	MHz		—	0.7	2.4	%
Minimum attenuation				α_{min}			
	50... 824	MHz		40	61	—	dB
	824... 849	MHz		40	60	—	dB
	849... 1710	MHz		40	50	—	dB
	1710... 1780	MHz		48	51	—	dB
	1780... 1850	MHz		30	47	—	dB
	1850... 1910	MHz		38	41	—	dB
	1910... 1990	MHz		35	37	—	dB
	1990... 2065	MHz		28	37	—	dB
	2240... 2400	MHz		14	46	—	dB
	2400... 2483	MHz		40	43	—	dB
	2483... 4600	MHz		28	32	—	dB
	4600... 5150	MHz		20	29	—	dB
	5150... 5850	MHz		20	28	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

²⁾ Integrated attenuation α_{INT} : Averaged power $|S_{ij}|^2$ over the center 4.5 MHz of LTE 5 MHz (25 RB) channels.

³⁾ Error Vector Magnitude (EVM) based on definition in 3GPP TS 25.141.

6.2 ANT – RX

Temperature range for specification
TX terminating impedance
ANT terminating impedance
RX terminating impedance

T_{SPEC} = -10 °C ... +85 °C
 Z_{TX} = 50 Ω // 5.5 nH¹⁾
 Z_{ANT} = 50 Ω // 2.7 nH¹⁾
 Z_{RX} = 50 Ω // 9.7 nH¹⁾

Characteristics ANT – RX			min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Center frequency		f_C	—	1745	—	MHz
Insertion attenuation		$\alpha_{INT}^{2)}$				
	1710... 1715	MHz	—	1.6	2.8	dB
	1715... 1775	MHz	—	1.8	2.6	dB
	1775... 1780	MHz	—	1.9	2.8	dB
Maximum insertion attenuation		α_{max}				
	1710... 1780	MHz	—	2.0	3.0	dB
Amplitude ripple (p-p)		$\Delta\alpha$				
	1710... 1780	MHz	—	0.8	1.8	dB
Maximum group delay		t_{max}				
	1712.5... 1777.5	MHz	—	20	35	ns
Group delay ripple		$\Delta\tau_{var}$				
	1712.5... 1777.5	MHz	—	9	25	ns
Maximum VSWR		VSWR _{max}				
@ ANT port	1710... 1780	MHz	—	1.5	2.0	
@ RX port	1710... 1780	MHz	—	1.6	2.0	
Maximum error vector magnitude		EVM _{max} ³⁾				
	1712.5... 1777.5	MHz	—	0.8	2.0	%
Minimum attenuation		α_{min}				
	50... 869	MHz	40	60	—	dB
	869... 894	MHz	40	59	—	dB
	894... 1660	MHz	30	45	—	dB
	1660... 1665	MHz	35	46	—	dB
	1665... 1690	MHz	10	16	—	dB
	1800... 1807	MHz	4	20	—	dB
	1807... 1815	MHz	15	34	—	dB
	1815... 1930	MHz	30	41	—	dB
	1930... 1990	MHz	40	47	—	dB
	1990... 2110	MHz	40	48	—	dB
	2110... 2200	MHz	46	48	—	dB
	2200... 2400	MHz	30	45	—	dB
	2400... 2483	MHz	30	45	—	dB
	2483... 5150	MHz	35	47	—	dB
	5150... 5850	MHz	25	39	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

²⁾ Integrated attenuation α_{INT} : Averaged power $|S_{ij}|^2$ over the center 4.5 MHz of LTE 5 MHz (25 RB) channels.

³⁾ Error Vector Magnitude (EVM) based on definition in 3GPP TS 25.141.

Temperature range for specification	T_{SPEC}	= -40 °C ... +95 °C
TX terminating impedance	Z_{TX}	= 50 Ω // 5.5 nH ¹⁾
ANT terminating impedance	Z_{ANT}	= 50 Ω // 2.7 nH ¹⁾
RX terminating impedance	Z_{RX}	= 50 Ω // 9.7 nH ¹⁾

Characteristics ANT – RX				min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Insertion attenuation				$\alpha_{INT}^{2)}$			
	1710... 1715	MHz		—	1.6	2.9	dB
	1715... 1775	MHz		—	1.8	2.7	dB
	1775... 1780	MHz		—	1.9	2.9	dB
Maximum insertion attenuation				α_{max}			
	1710... 1780	MHz		—	2.1	3.2	dB
Amplitude ripple (p-p)				$\Delta\alpha$			
	1710... 1780	MHz		—	0.7	2.3	dB
Maximum group delay				t_{max}			
	1712.5... 1777.5	MHz		—	20	40	ns
Group delay ripple				$\Delta\tau_{var}$			
	1712.5... 1777.5	MHz		—	9	30	ns
Maximum VSWR				VSWR _{max}			
@ ANT port	1710... 1780	MHz		—	1.5	2.1	
@ RX port	1710... 1780	MHz		—	1.6	2.0	
Maximum error vector magnitude				EVM _{max} ³⁾			
	1712.5... 1777.5	MHz		—	0.8	2.8	%
Minimum attenuation				α_{min}			
	50... 869	MHz		40	60	—	dB
	869... 894	MHz		40	59	—	dB
	894... 1660	MHz		30	45	—	dB
	1660... 1665	MHz		35	46	—	dB
	1665... 1690	MHz		10	16	—	dB
	1803... 1807	MHz		4	20	—	dB
	1807... 1815	MHz		11	34	—	dB
	1815... 1930	MHz		28	41	—	dB
	1930... 1990	MHz		40	47	—	dB
	1990... 2110	MHz		40	48	—	dB
	2110... 2200	MHz		46	48	—	dB
	2200... 2400	MHz		30	45	—	dB
	2400... 2483	MHz		30	45	—	dB
	2483... 5150	MHz		35	47	—	dB
	5150... 5850	MHz		25	39	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

²⁾ Integrated attenuation α_{INT} : Averaged power $|S_{ij}|^2$ over the center 4.5 MHz of LTE 5 MHz (25 RB) channels.

³⁾ Error Vector Magnitude (EVM) based on definition in 3GPP TS 25.141.

6.3 TX – RX

Temperature range for specification	T_{SPEC}	= -10 °C ... +85 °C
TX terminating impedance	Z_{TX}	= 50 Ω // 5.5 nH ¹⁾
ANT terminating impedance	Z_{ANT}	= 50 Ω // 2.7 nH ¹⁾
RX terminating impedance	Z_{RX}	= 50 Ω // 9.7 nH ¹⁾

Characteristics TX – RX			min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Isolation	$\alpha_{INT}^{2)}$	1710... 1780 MHz	50	54	—	dB
		1780... 2110 MHz	48	50	—	dB
		2110... 2200 MHz	50	53	—	dB
	α_{min}					
Minimum isolation	α_{min}	1710... 1780 MHz	50	54	—	dB
		1780... 2110 MHz	48	50	—	dB
		2110... 2200 MHz	50	53	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

²⁾ Integrated attenuation α_{INT} : Averaged power $|S_{ij}|^2$ over the center 4.5 MHz of LTE 5 MHz (25 RB) channels.

Temperature range for specification	T_{SPEC}	= -40 °C ... +95 °C
TX terminating impedance	Z_{TX}	= 50 Ω // 5.5 nH ¹⁾
ANT terminating impedance	Z_{ANT}	= 50 Ω // 2.7 nH ¹⁾
RX terminating impedance	Z_{RX}	= 50 Ω // 9.7 nH ¹⁾

Characteristics TX – RX			min. for T_{SPEC}	typ. @ +25 °C	max. for T_{SPEC}	
Isolation	1710... 1780 MHz	α_{INT} ²⁾	50	54	—	dB
			48	50	—	dB
			50	53	—	dB
Minimum isolation	1710... 1780 MHz	α_{min}	50	54	—	dB
			48	50	—	dB
			50	53	—	dB

¹⁾ See Sec. Matching circuit (p. 6).

²⁾ Integrated attenuation α_{INT} : Averaged power $|S_{ij}|^2$ over the center 4.5 MHz of LTE 5 MHz (25 RB) channels.

7 Maximum ratings

Operable temperature	$T_{OP} = -40\text{ °C} \dots +95\text{ °C}$	
Storage temperature	$T_{STG}^{1)} = -40\text{ °C} \dots +95\text{ °C}$	
DC voltage	$ V_{DC} ^{2)} = 0\text{ V}$	
ESD voltage		
	$V_{ESD}^{3)} = 250\text{ V}$	Human body model.
	$V_{ESD}^{4)} = 125\text{ V}$	Machine model.
Input power	P_{IN}	
@ TX port: 2110 ... 2200 MHz	28 dBm ^{5), 6)}	5 MHz LTE downlink signal (25 RB) for 100000 h @ 55 °C. P_{IN} average – 39 dBm peak. Source and load impedance 50Ω.
@ RX port: 1710 ... 1780 MHz	23 dBm ^{5), 7)}	5 MHz LTE uplink signal (25 RB) for 5000 h @ 55 °C. P_{IN} average – 39 dBm peak. Source and load impedance 50Ω.

¹⁾ Not valid for packaging material. Storage temperature for packaging material is –25 °C to +40 °C.

²⁾ In case of applied DC voltage blocking capacitors are mandatory.

³⁾ According to JESD22-A114F (HBM – Human Body Model), 1 negative & 1 positive pulse.

⁴⁾ According to JESD22-A115B (MM – Machine Model), 10 negative & 10 positive pulses.

⁵⁾ Expected lifetime according to accelerated power durability test and wear out models.

⁶⁾ T_{SPEC} is the ambient temperature of the PCB at component position. Specified min./max values from section 6 "characteristics" for maximum input power 28 dBm are valid for temperature up to 55 °C.

⁷⁾ T_{SPEC} is the ambient temperature of the PCB at component position. Specified min./max values from section 7 "characteristics" for maximum input power 23 dBm are valid for temperature up to 55 °C.

8 Transmission coefficients

8.1 TX – ANT

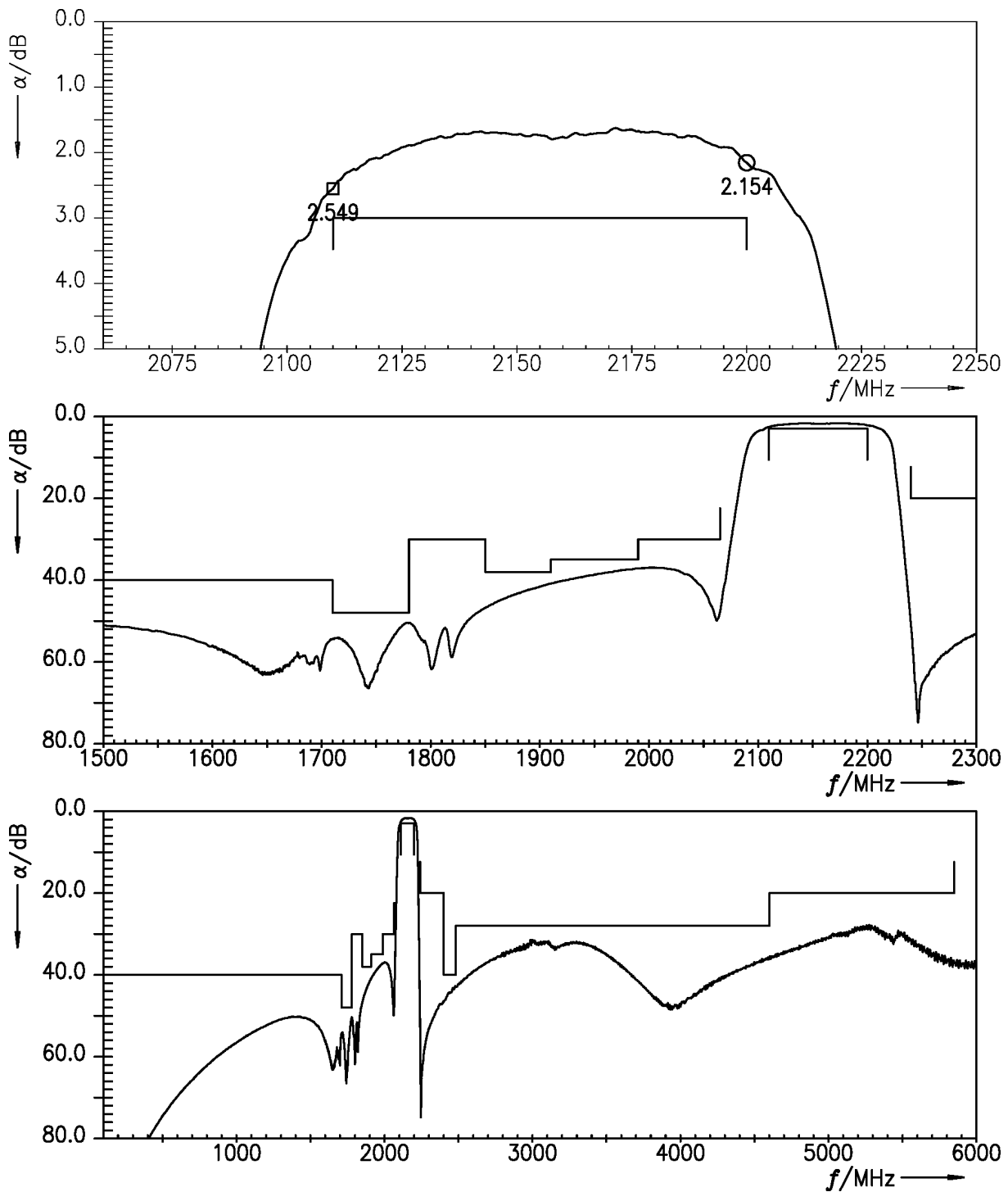


Figure 4: Attenuation TX – ANT.

8.2 ANT – RX

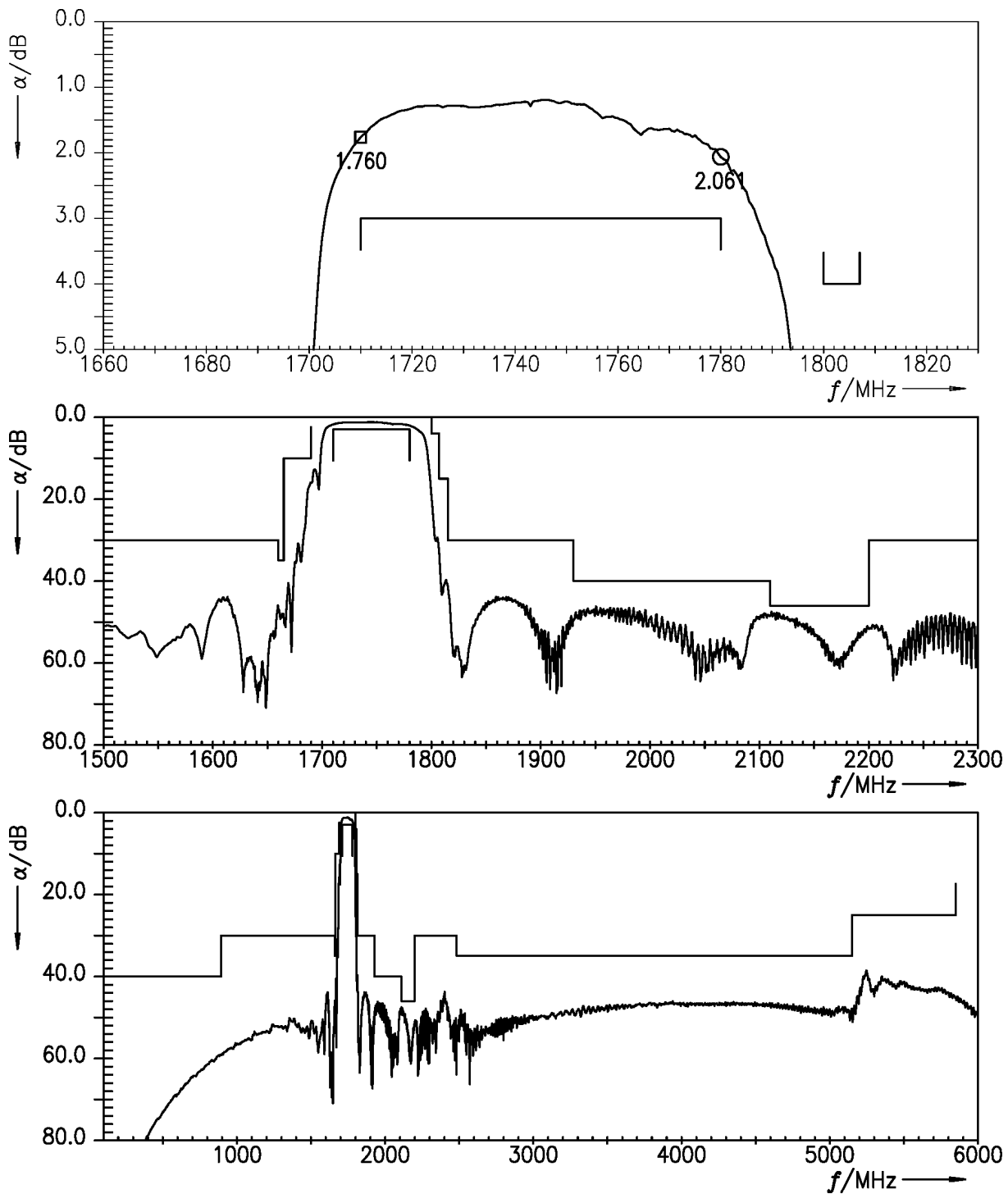


Figure 5: Attenuation ANT – RX.

8.3 TX – RX

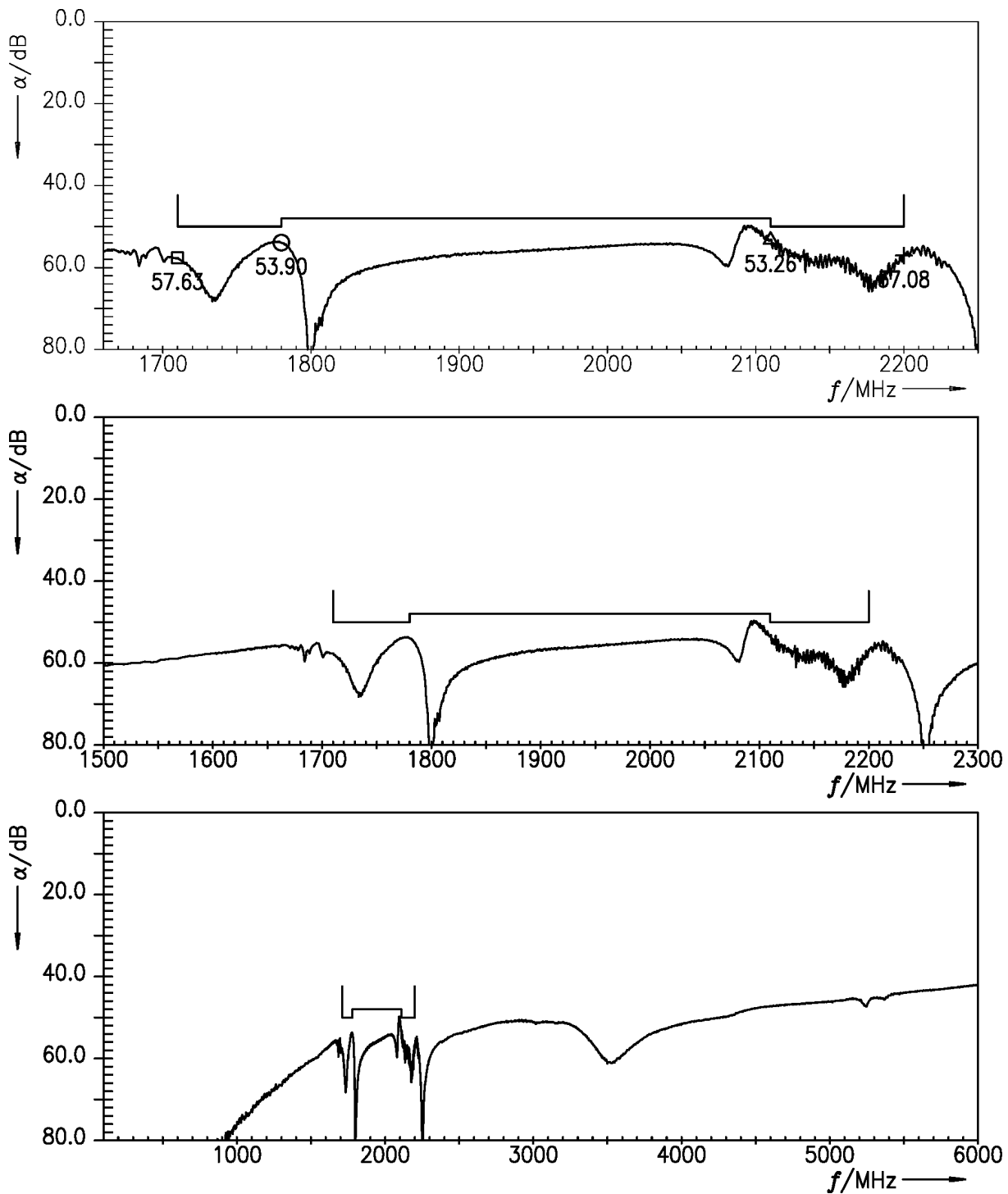


Figure 6: Isolation TX – RX.

9 Reflection coefficients

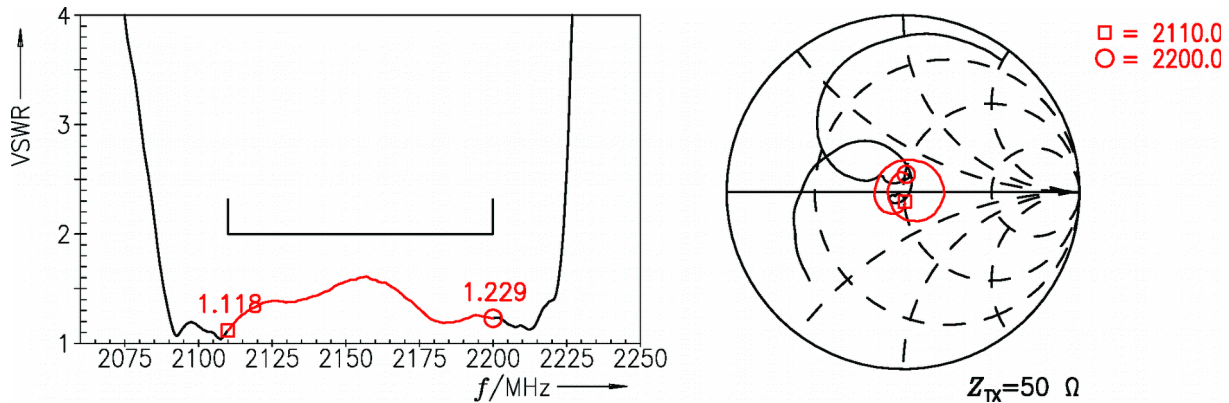


Figure 7: Reflection coefficient at TX port.

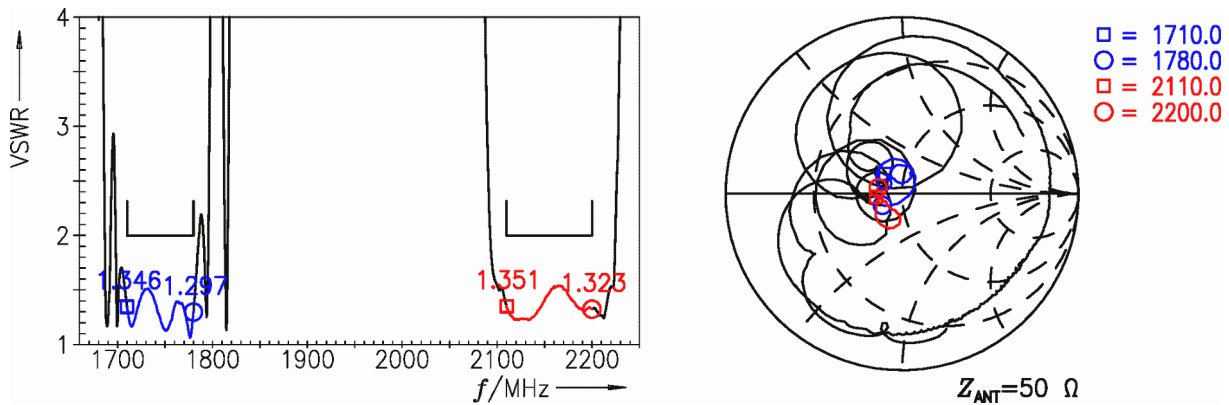


Figure 8: Reflection coefficient at ANT port.

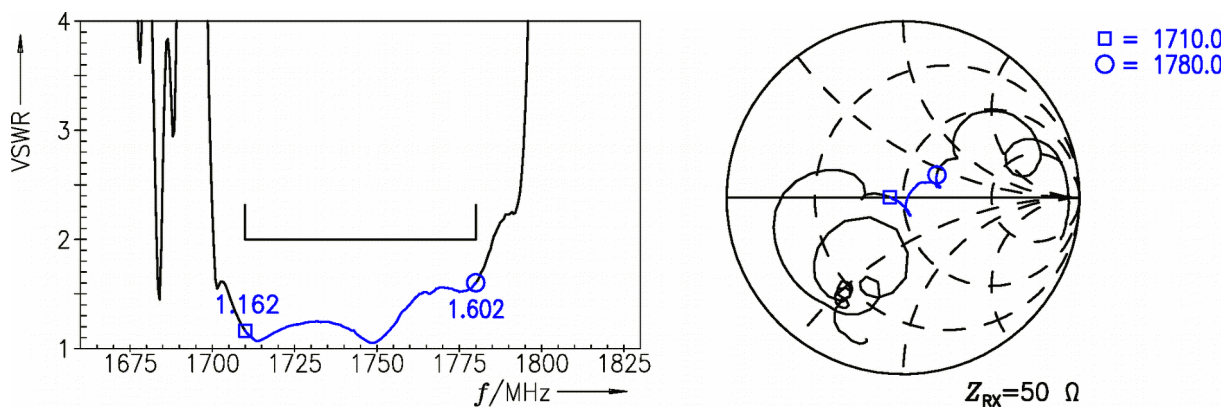


Figure 9: Reflection coefficient at RX port.

10 EVMs

10.1 TX – ANT

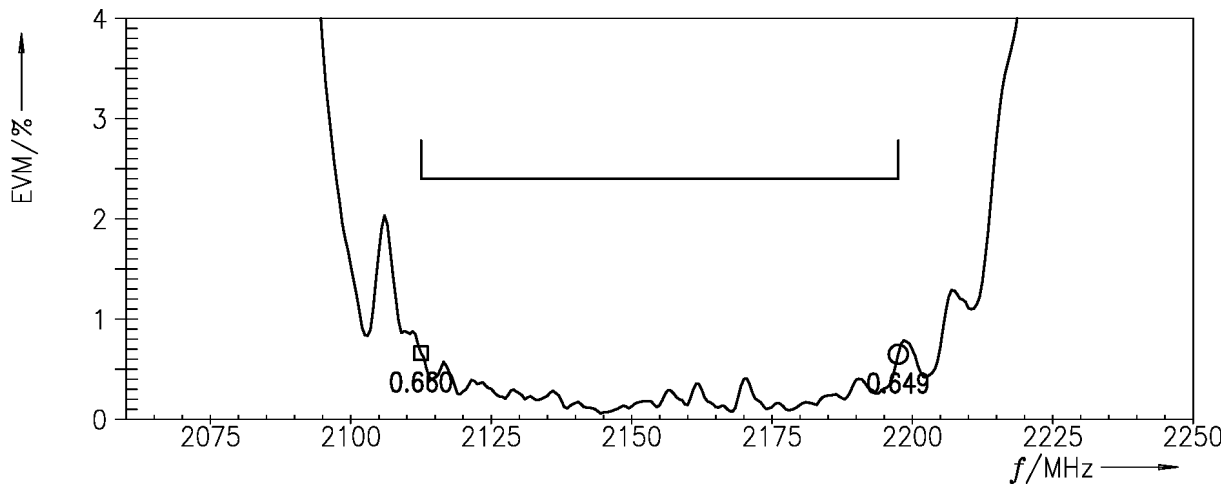


Figure 10: Error vector magnitude TX – ANT.

10.2 ANT – RX

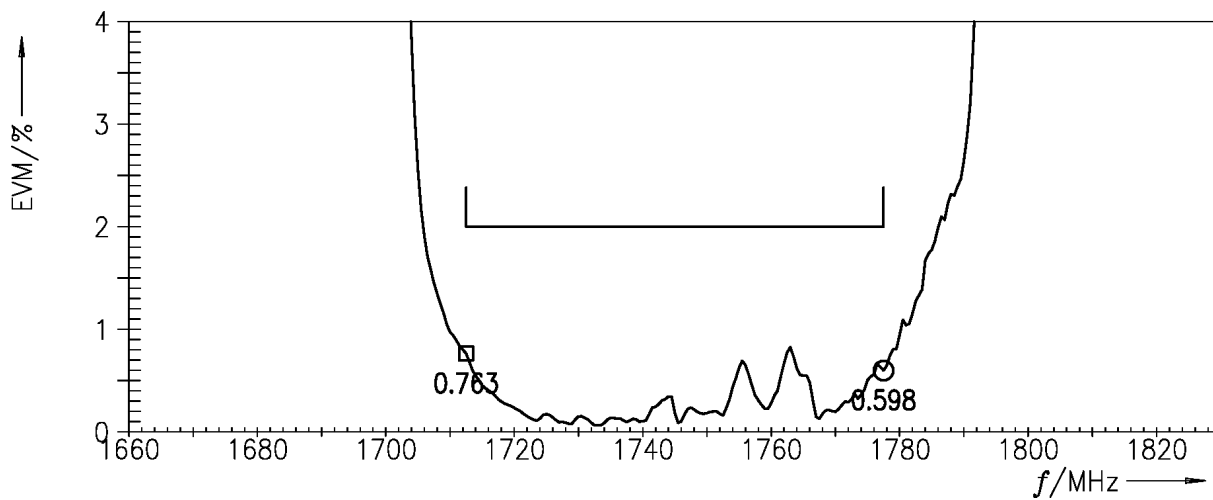


Figure 11: Error vector magnitude ANT – RX.

11 Group delay

11.1 TX – ANT

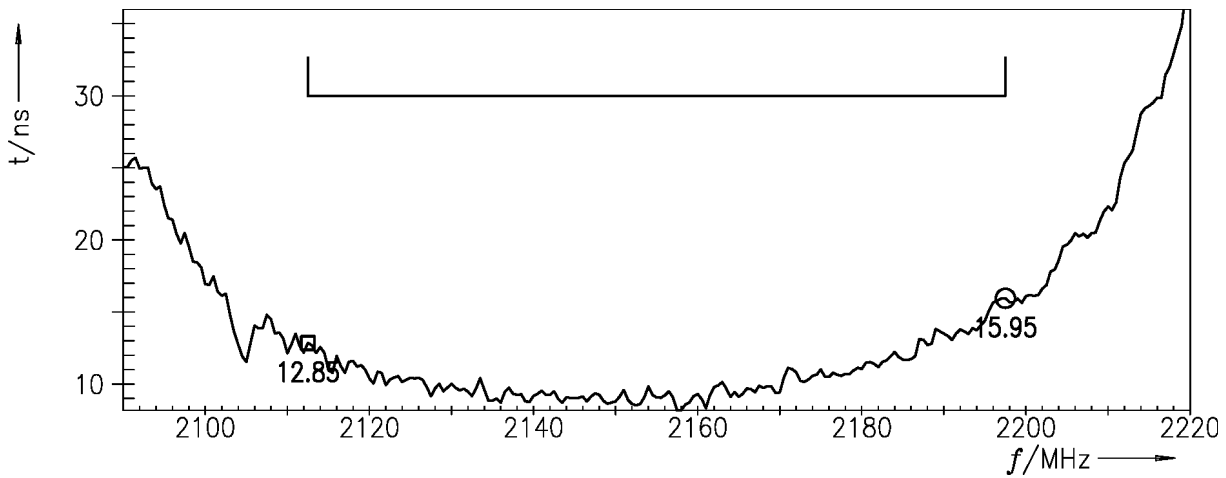


Figure 12: Group delay TX – ANT.

11.2 ANT – RX

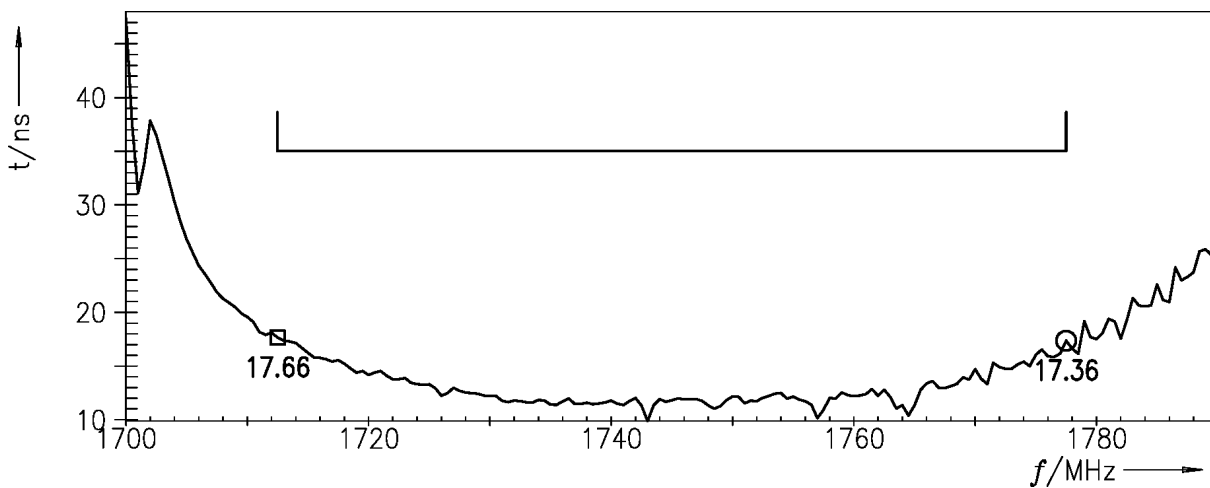


Figure 13: Group delay ANT – RX.

12 Packing material

12.1 Tape

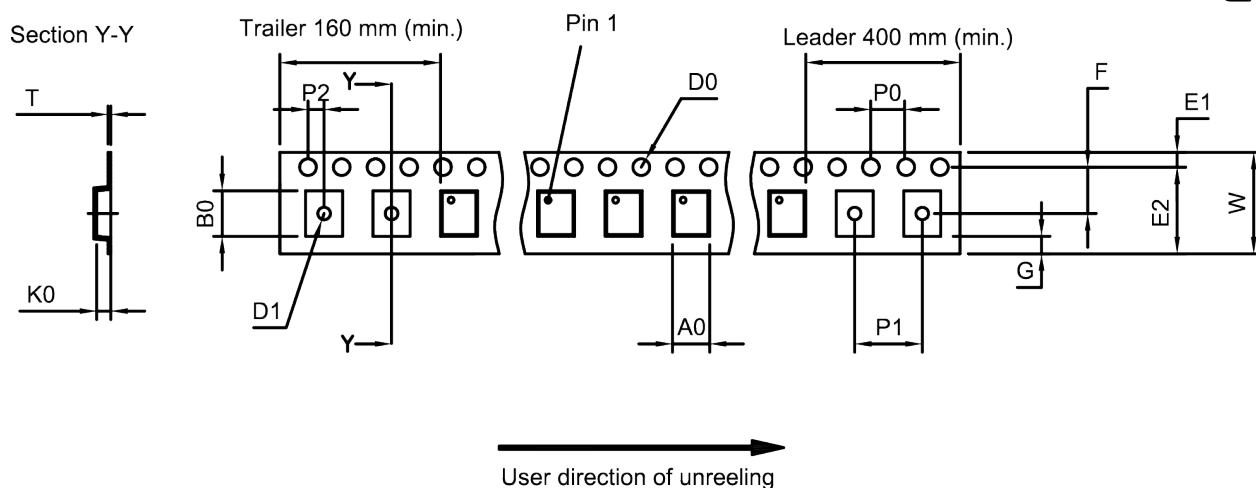


Figure 14: Drawing of tape (first-angle projection) for illustration only and not to scale. The valid tape dimensions are listed in Table 1.

A_0	2.25 ± 0.05 mm	E_2	6.25 mm (min.)	P_1	4.0 ± 0.1 mm
B_0	2.75 ± 0.05 mm	F	3.5 ± 0.05 mm	P_2	2.0 ± 0.05 mm
D_0	$1.5 + 0.1 / - 0$ mm	G	0.75 mm (min.)	T	0.25 ± 0.03 mm
D_1	1.0 mm (min.)	K_0	0.6 ± 0.05 mm	W	$8.0 + 0.3 / - 0.1$ mm
E_1	1.75 ± 0.1 mm	P_0	4.0 ± 0.1 mm		

Table 1: Tape dimensions.

12.2 Reel with diameter of 180 mm

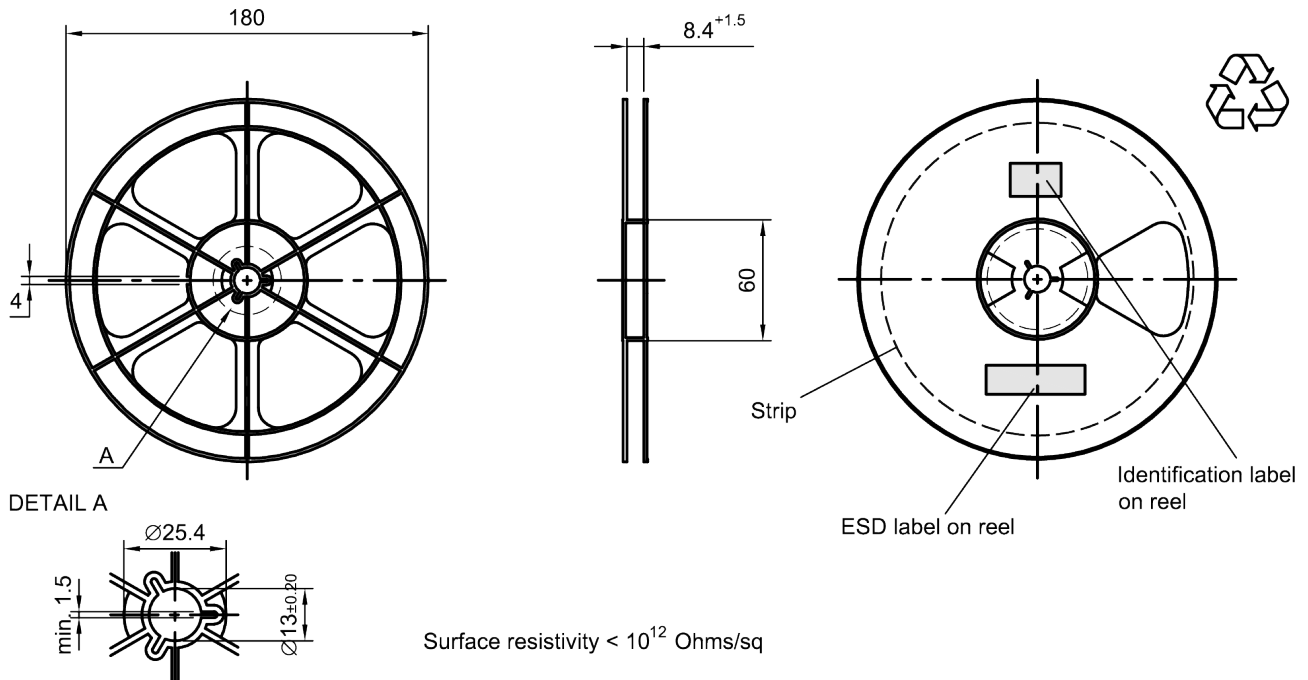


Figure 15: Drawing of reel (first-angle projection) with diameter of 180 mm.

Dimensions [mm]

X = 220+5

Y = 235+5

Sealing area 10±3

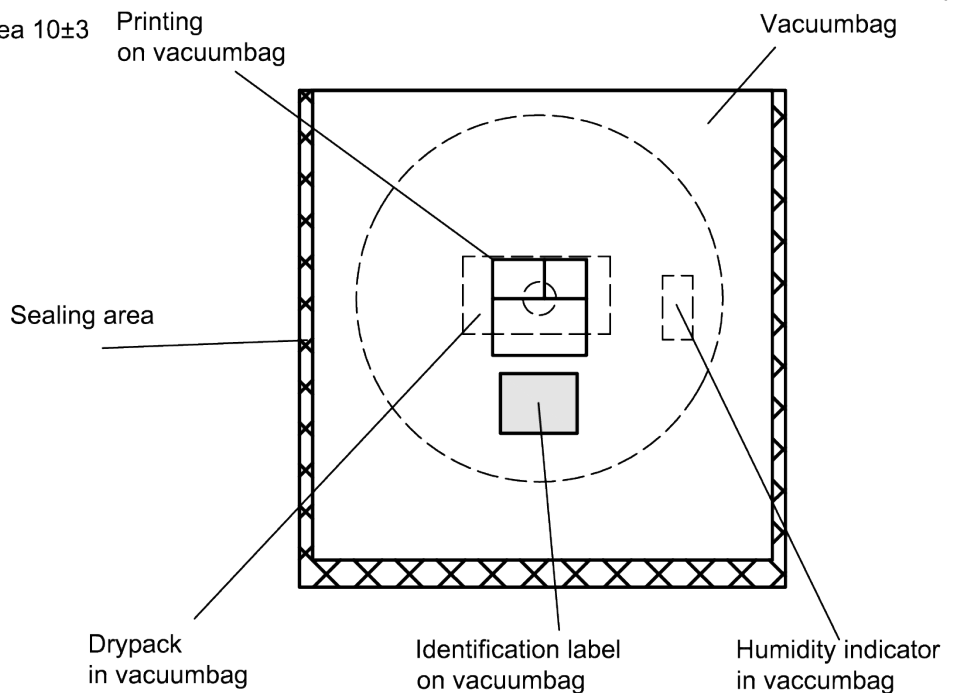


Figure 16: Drawing of moisture barrier bag (MBB) for reel with diameter of 180 mm.

Dimensions [mm]

L = 188

B = 188

H = 30

Tolerance ± 5

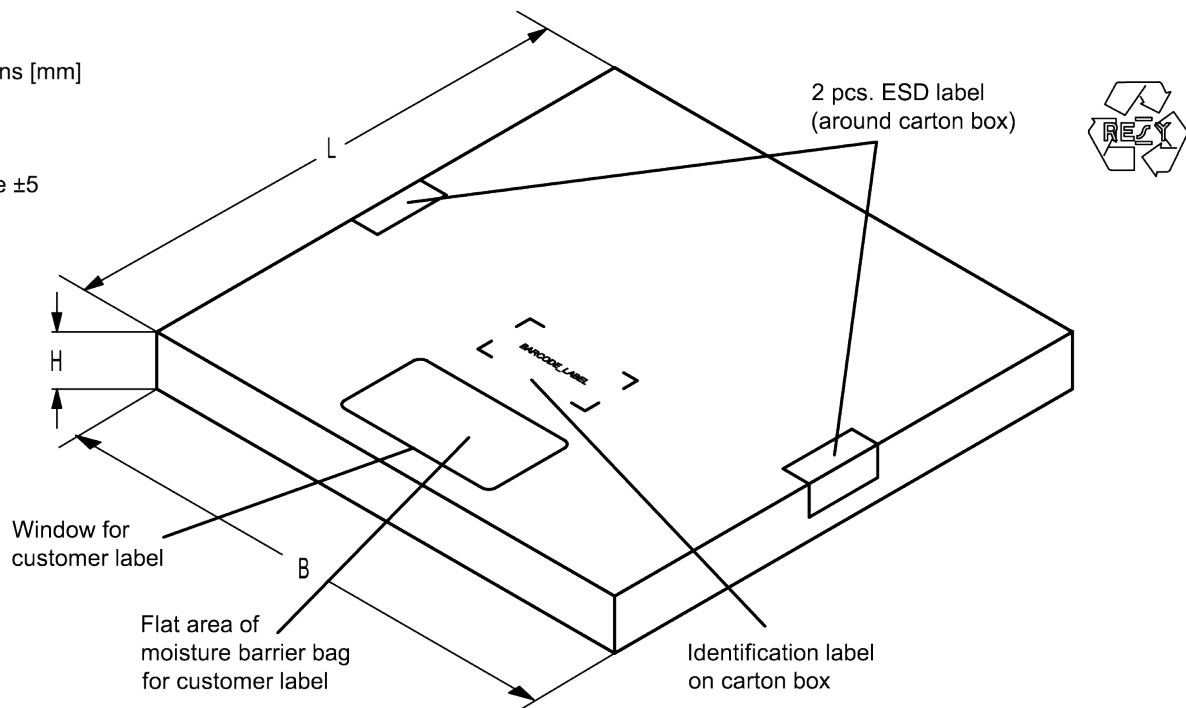


Figure 17: Drawing of folding box for reel with diameter of 180 mm.

12.3 Reel with diameter of 330 mm

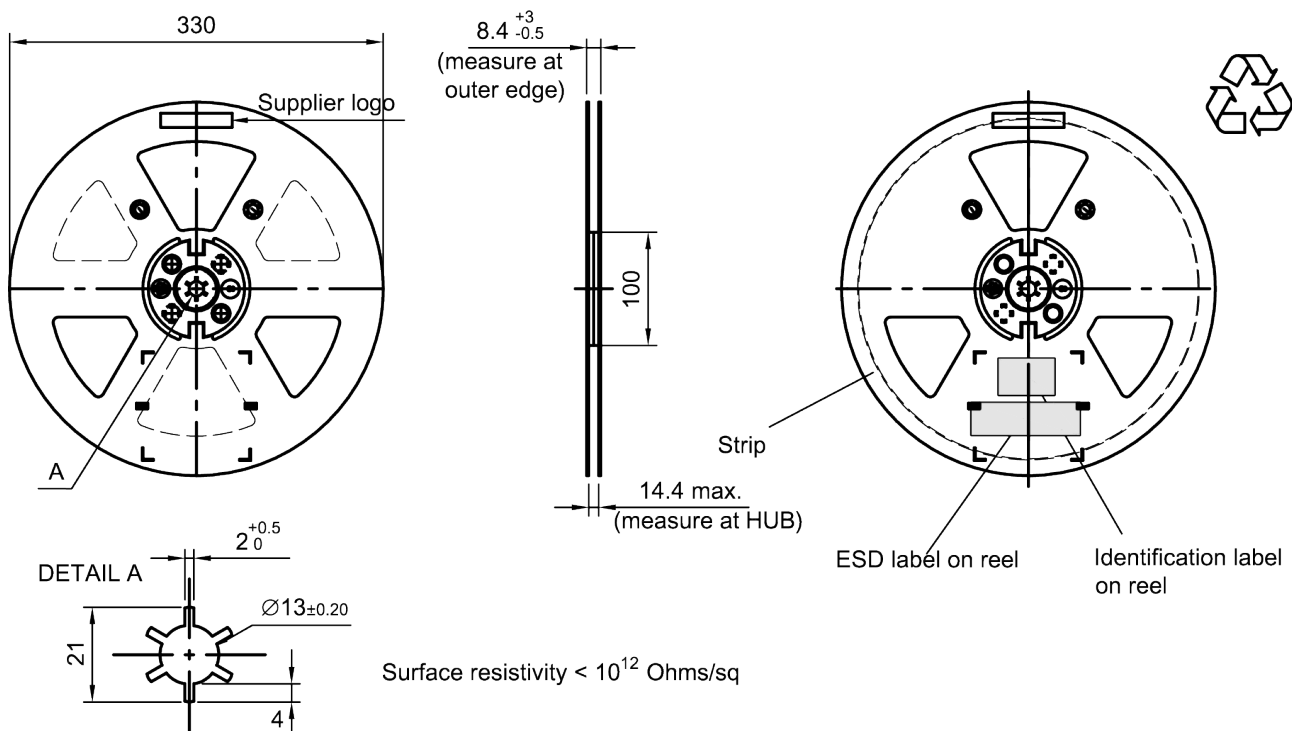


Figure 18: Drawing of reel (first-angle projection) with diameter of 330 mm.

Dimensions [mm]

X = 400+5

Y = 418+5

Sealing area 10±3

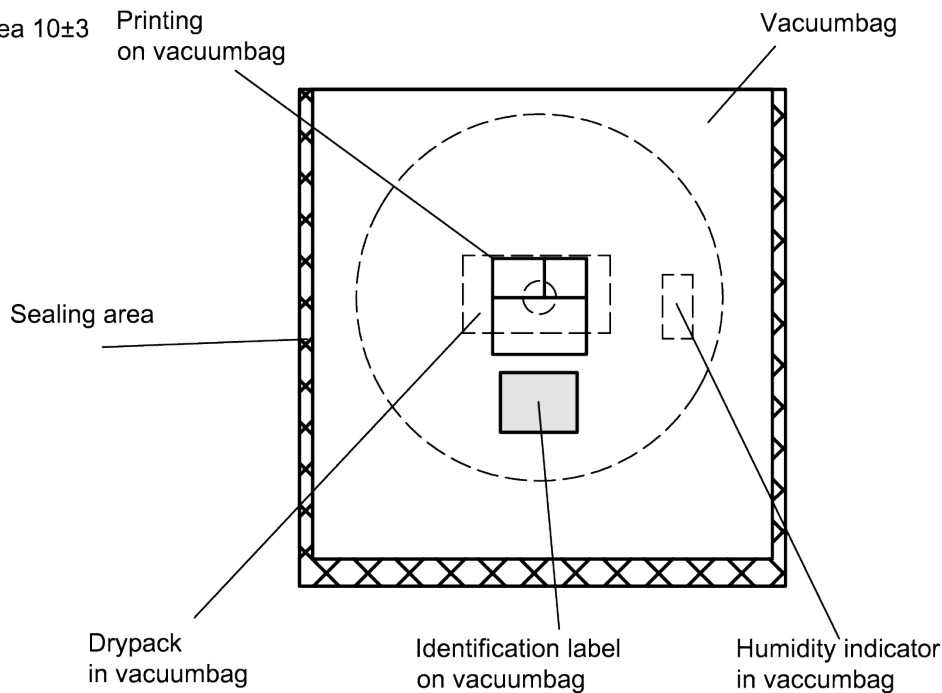


Figure 19: Drawing of moisture barrier bag (MBB) for reel with diameter of 330 mm.

Dimensions [mm]

L = 335

B = 338

H = 36 (for 8 mm tape width)
40 (for 12 mm tape width)

Tolerance ±5

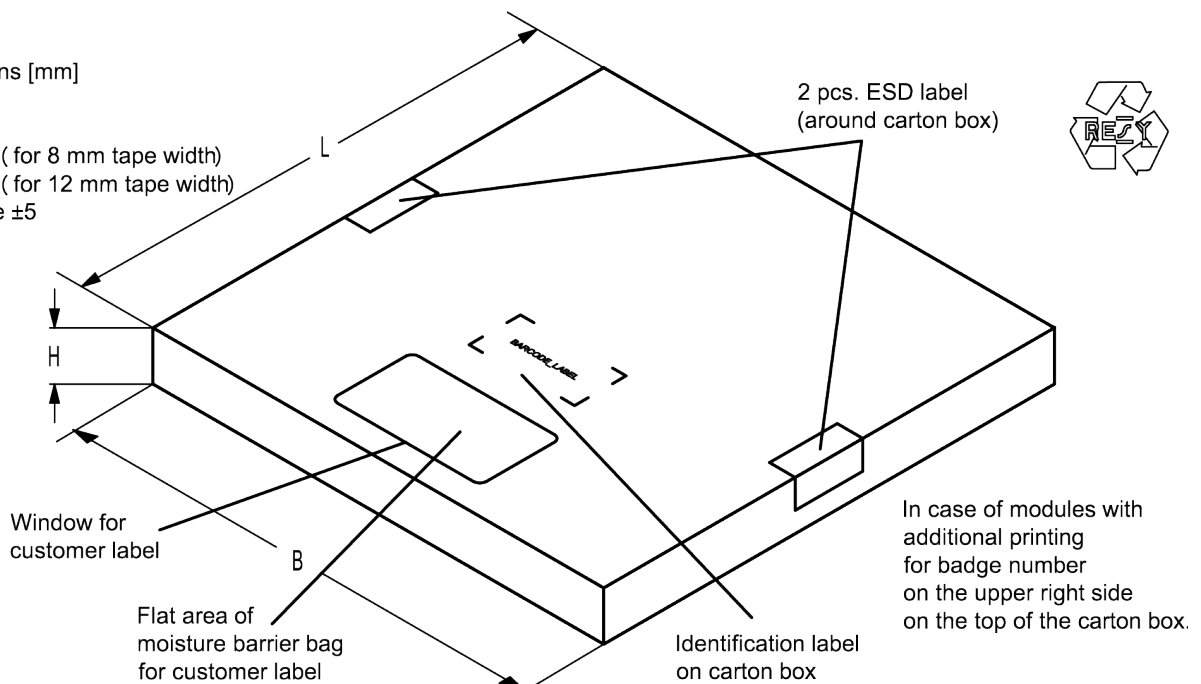


Figure 20: Drawing of folding box for reel with diameter of 330 mm.

13 Marking

Products are marked with product type number and lot number encoded according to Table 2:

■ Type number:

The 4 digit type number of the ordering code, e.g., B3xxxxB**1234**xxxx,
is encoded by a special BASE32 code into a 3 digit marking.

Example of decoding type number marking on device in decimal code.
16J \Rightarrow **1234**
 $1 \times 32^2 + 6 \times 32^1 + 18 (=J) \times 32^0 =$ **1234**
 The BASE32 code for product type B8206 is 80E.

■ Lot number:

The last 5 digits of the lot number, e.g., **12345**,
are encoded based on a special BASE47 code into a 3 digit marking.

Example of decoding lot number marking on device in decimal code.
5UY \Rightarrow **12345**
 $5 \times 47^2 + 27 (=U) \times 47^1 + 31 (=Y) \times 47^0 =$ **12345**

Adopted BASE32 code for type number			
Decimal value	Base32 code	Decimal value	Base32 code
0	0	16	G
1	1	17	H
2	2	18	J
3	3	19	K
4	4	20	M
5	5	21	N
6	6	22	P
7	7	23	Q
8	8	24	R
9	9	25	S
10	A	26	T
11	B	27	V
12	C	28	W
13	D	29	X
14	E	30	Y
15	F	31	Z

Adopted BASE47 code for lot number			
Decimal value	Base47 code	Decimal value	Base47 code
0	0	24	R
1	1	25	S
2	2	26	T
3	3	27	U
4	4	28	V
5	5	29	W
6	6	30	X
7	7	31	Y
8	8	32	Z
9	9	33	b
10	A	34	d
11	B	35	f
12	C	36	h
13	D	37	n
14	E	38	r
15	F	39	t
16	G	40	v
17	H	41	\
18	J	42	?
19	K	43	{
20	L	44	}
21	M	45	<
22	N	46	>
23	P		

Table 2: Lists for encoding and decoding of marking.

14 Soldering profile

The recommended soldering process is in accordance with IEC 60068-2-58 – 3rd edit and IPC/JEDEC J-STD-020B.

ramp rate	≤ 3 K/s
preheat	125 °C to 220 °C, 150 s to 210 s, 0.4 K/s to 1.0 K/s
$T > 220\text{ °C}$	30 s to 70 s
$T > 230\text{ °C}$	min. 10 s
$T > 245\text{ °C}$	max. 20 s
$T \geq 255\text{ °C}$	–
peak temperature T_{peak}	250 °C +0/-5 °C
wetting temperature T_{min}	230 °C +5/-0 °C for 10 s ± 1 s
cooling rate	≤ 3 K/s
soldering temperature T	measured at solder pads

Table 3: Characteristics of recommended soldering profile for lead-free solder (Sn95.5Ag3.8Cu0.7).

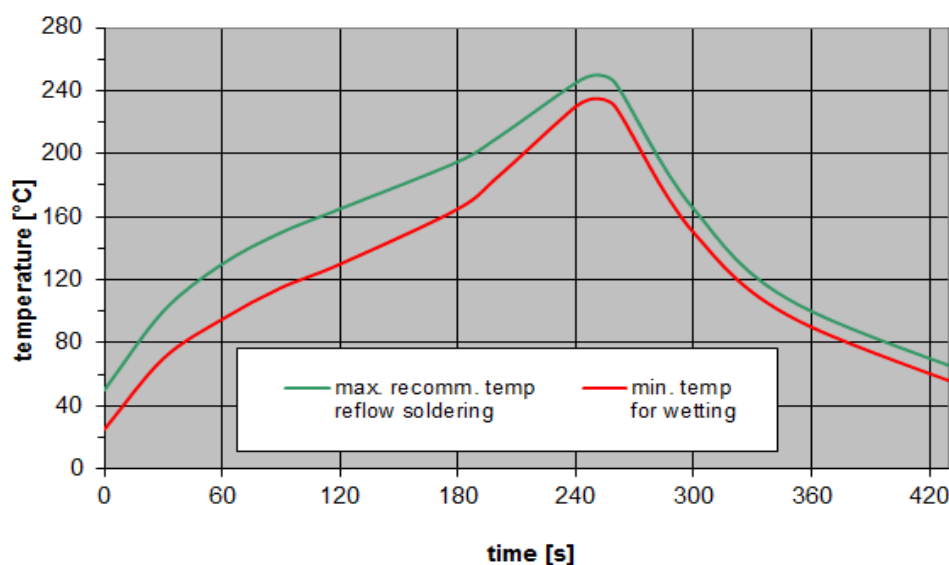


Figure 21: Recommended reflow profile for convection and infrared soldering – lead-free solder.

15 Annotations

15.1 RoHS compatibility

ROHS-compatible means that products are compatible with the requirements according to Art. 4 (substance restrictions) of Directive 2011/65/EU of the European Parliament and of the Council of June 8th, 2011, on the restriction of the use of certain hazardous substances in electrical and electronic equipment ("Directive") with due regard to the application of exemptions as per Annex III of the Directive in certain cases.

15.2 Scattering parameters (S-parameters)

The pin/port assignment is available in the headers of the S-parameter files. Please contact your local RF360 sales office.

16 Cautions and warnings

16.1 Display of ordering codes for RF360 products

The ordering code for one and the same product can be represented differently in data sheets, data books, other publications and the website of RF360, or in order-related documents such as shipping notes, order confirmations and product labels. The varying representations of the ordering codes are due to different processes employed and do not affect the specifications of the respective products. Detailed information can be found on the Internet under <https://rfe.qualcomm.com/>.

16.2 Material information

Due to technical requirements components may contain dangerous substances. For information on the type in question please also contact one of our sales offices.

For information on recycling of tapes and reels please contact one of our sales offices.

16.3 Moldability

Before using in overmolding environment, please contact your local RF360 sales office.

16.4 Package information

Landing area

The printed circuit board (PCB) land pattern (landing area) shown is based on RF360 internal development and empirical data and illustrated for example purposes, only. As customers' SMD assembly processes may have a plenty of variants and influence factors which are not under control or knowledge of RF360, additional careful process development on customer side is necessary and strongly recommended in order to achieve best soldering results tailored to the particular customer needs.

Dimensions

Unless otherwise specified all dimensions are understood using unit millimeter (mm).

Dimensions do not include burrs.

Projection method

Unless otherwise specified first-angle projection is applied.

17 ESD protection of SAW filters

SAW filters are **E**lectro **S**tatic **D**ischarge sensitive devices. To reduce the probability of damages caused by ESD, special matching topologies have to be applied.

In general, “ESD matching” has to be ensured at that filter port, where electrostatic discharge is expected.

Electrostatic discharges predominantly appear at the antenna input of RF receivers. Therefore, only the input matching of the SAW filter has to be designed to short circuit or to block the ESD pulse.

Below three figures show recommended “ESD matching” topologies.

For wide band filters the high-pass ESD matching structure needs to be at least of 3rd order to ensure a proper matching for any impedance value of antenna and SAW filter input. The required component values have to be determined from case to case.

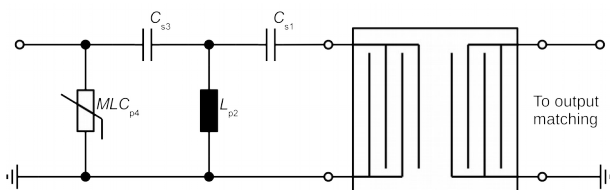


Figure 22: MLC varistor plus ESD matching.

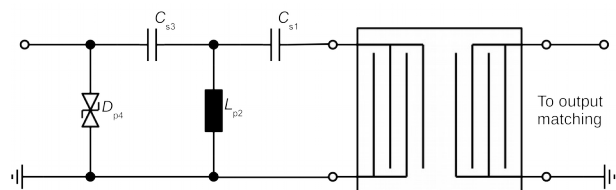


Figure 23: Suppressor diode plus ESD matching.

In cases where minor ESD occur, following simplified “ESD matching” topologies can be used alternatively.

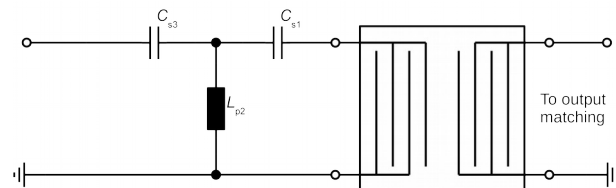


Figure 24: 3rd order high-pass structure for basic ESD protection.

In all three figures the shunt inductor L_{p2} could be replaced by a shorted microstrip with proper length and width. If this configuration is possible depends on the operating frequency and available PCB space.

Effectiveness of the applied ESD protection has to be checked according to relevant industry standards or customer specific requirements.

For further information, please refer to RF360 Application report: “**ESD protection for SAW filters**”. This report can be found under <https://rffe.qualcomm.com>.

18 Important notes

The following applies to all products named in this publication:

1. Some parts of this publication contain **statements about the suitability of our products for certain areas of application**. These statements are based on our knowledge of typical requirements that are often placed on our products in the areas of application concerned. We nevertheless expressly point out **that such statements cannot be regarded as binding statements about the suitability of our products for a particular customer application**. As a rule, RF360 Europe GmbH and its affiliates are either unfamiliar with individual customer applications or less familiar with them than the customers themselves. For these reasons, it is always ultimately incumbent on the customer to check and decide whether an RF360 product with the properties described in the product specification is suitable for use in a particular customer application.
2. We also point out that **in individual cases, a malfunction of electronic components or failure before the end of their usual service life cannot be completely ruled out in the current state of the art, even if they are operated as specified**. In customer applications requiring a very high level of operational safety and especially in customer applications in which the malfunction or failure of an electronic component could endanger human life or health (e.g. in accident prevention or life-saving systems), it must therefore be ensured by means of suitable design of the customer application or other action taken by the customer (e.g. installation of protective circuitry or redundancy) that no injury or damage is sustained by third parties in the event of malfunction or failure of an electronic component.
3. **The warnings, cautions and product-specific notes must be observed.**
4. In order to satisfy certain technical requirements, **some of the products described in this publication may contain substances subject to restrictions in certain jurisdictions (e.g. because they are classed as hazardous)**. Useful information on this will be found in our Material Data Sheets on the Internet (<https://rfe.qualcomm.com>). Should you have any more detailed questions, please contact our sales offices.
5. We constantly strive to improve our products. Consequently, **the products described in this publication may change from time to time**. The same is true of the corresponding product specifications. Please check therefore to what extent product descriptions and specifications contained in this publication are still applicable before or when you place an order. We also **reserve the right to discontinue production and delivery of products**. Consequently, we cannot guarantee that all products named in this publication will always be available.
The aforementioned does not apply in the case of individual agreements deviating from the foregoing for customer-specific products.